

B1
conc. treatment which is performed through the lamp annealing furnace immediately after deposition of the metal film 9 is hereafter referred to as first RTA.

Please replace the paragraph at page 2, line 23, through page 3, line 8, with the following text:

B2 However, when the silicide films formed through the aforementioned process are made of titanium silicide TiSi_x , for example, further heat treatment is performed at a high temperature or over a long time for forming titanium silicide films of TiSi_2 having a different composition or structure, since the electric properties of titanium silicide TiSi_x are insufficient. Also in case of changing the composition or structure of titanium silicide, a short-time heat treatment is generally performed through a lamp annealing furnace. The short-time heat treatment employed for changing the composition or structure of such silicide films is hereinafter referred to as second RTA. Due to the silicide process employing the aforementioned steps, an electrode can advantageously be formed selectively only on a region exposing a silicon surface on the silicon substrate 1.

IN THE CLAIMS

Please cancel Claims 1-9 without prejudice.

REMARKS

Favorable consideration of this application, as presently amended, is respectfully requested.

The present new application is a divisional of copending parent U.S. application serial no. 08/874,410.